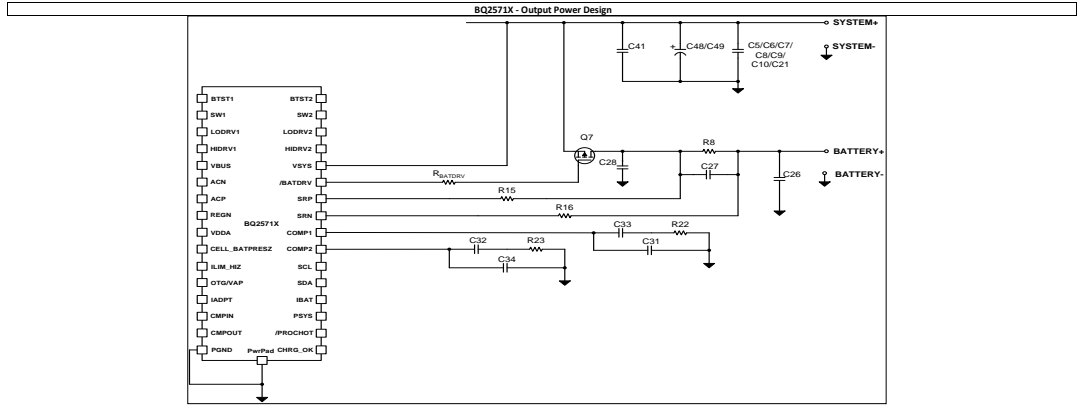
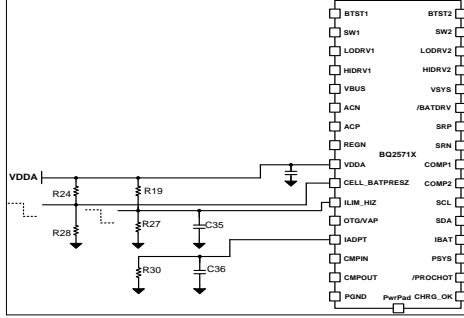


INPUT POWER - DESIGN CHECKLIST								
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS	
ADAPTER / ADAPTER	Required	C1-C4/C3-C4 C44-C45	40 uF	60 uF		Forward Mode: Ceramic high frequency filtering input capacitors. Reverse Mode: Converter ceramic output filtering capacitors.	Input source to the charger For a 45 W to 65 W 5% load, use at least (4x) 10 uF capacitors with an extra (2x) 10 uF DNP. For a 90 W to 65 W 5% load, use at least (6x) 10 uF capacitors with an extra (2x) 10 uF DNP.	
	Required	C53	33 uF			Forward Mode: Tantalum polymer high frequency filtering input capacitor. Reverse Mode: Converter tantalum polymer output filtering capacitor.	For > 65W 5% loads, with a 4S battery configuration, use at least (1x) 33 uF tantalum polymer capacitor.	
	Recommended DNP	R3, R4	3.9 Ω				For systems with high input cable or trace inductance and hot plug use cases, add experimentally derived RC snubber to limit inrush current and input voltage overshoot. R3 and R4 in parallel should be sized appropriately to handle the inrush current.	
		C18	1 uF				Input hot plug snubber circuit	$R3  R4 = \frac{1}{\omega} \frac{I_{inrush,peak}}{I_{input,rms}} \text{ where } 0 < I_{inrush,peak} < I_{input,rms}$
	Optional	Q5, Q6					Back-to-Back input protection P-Ch MOSFETs.	Size Q5 and Q6 appropriately to handle input power, optimize losses, and allow for smooth turn-on and turn-off.
	Optional	R10, R11, R12, R13, R14, R15, R16, R17, R18, R19, R20, R21, R22, R23, R24, R25, R26, R27, R28, R29, R30, R31, R32, R33, R34, R35, R36, R37, R38, R39, R40, R41, R42, R43, R44, R45, R46, R47, R48, R49, R50, R51, R52, R53, R54, R55, R56, R57, R58, R59, R60, R61, R62, R63, R64, R65, R66, R67, R68, R69, R70, R71, R72, R73, R74, R75, R76, R77, R78, R79, R80, R81, R82, R83, R84, R85, R86, R87, R88, R89, R90, R91, R92, R93, R94, R95, R96, R97, R98, R99, R100					Input protection turn-on/turn-off delay	Note: If the Q5 and Q6 input protection circuit and is to function correctly, R13 (See VBUS) must be connected to the Drain of Q5.
	Optional	C22, C23, C24, C25, C26, C27, C28, C29, C30, C31, C32, C33, C34, C35, C36, C37, C38, C39, C40, C41, C42, C43, C44, C45, C46, C47, C48, C49, C50, C51, C52, C53, C54, C55, C56, C57, C58, C59, C60, C61, C62, C63, C64, C65, C66, C67, C68, C69, C70, C71, C72, C73, C74, C75, C76, C77, C78, C79, C80, C81, C82, C83, C84, C85, C86, C87, C88, C89, C90, C91, C92, C93, C94, C95, C96, C97, C98, C99, C100					Input protection turn-on/turn-off control	
Optional	Z1					Input protection gate-source Zener clamping diode.	Size to clamp maximum allowable VGS for Q5 and Q6.	
ACF-ACN	3-2	Required	R2 (R <sub>in</sub> )	10 mΩ	10 mΩ	20 mΩ	Differential input current sensing. Input current sensing resistor. This is used for both input current limit regulation and for inductor current sensing of the average current mode control architecture of the charger.	For higher accuracy at light loads, increase to 20 mΩ. This will impact the IADPT and PSYS pin measurements. In INPM1 regulation, the input current limit is regulated as a differential voltage across R <sub>in</sub> , such that: V <sub>in</sub> = R <sub>in</sub> × Minimum(IN_HOST) Register Setting, IN_DPM[3] Register Setting, ILM_HZ pin setting.
		Recommended	R11, R12, C46, C47	4.99 Ω	33 Ω		Input current sense switching noise and common mode noise filtering.	Select R11 / C46 and R12 / C47 such that the filter time constant is between 47 ns and 200 ns.
		Recommended	C12	10 nF	100 nF		High frequency switching current spike filtering.	Note: Too high of a capacitance on this side of RAC could impact the converter stability. This is the reason for limiting the maximum capacitance to 100nF.
		Recommended DNP	C11	0.01 uF			Differential mode noise filtering.	
VBUS	1	Required	C25	0.47 uF	0.47 uF		Input voltage noise decoupling capacitor.	Placed close to the IC VBUS pin. X7R capacitor is recommended.
		Recommended	R13	1 Ω			Input voltage rail inrush current limiting.	Size appropriately to handle large input overshoots and current spikes.
REGN	28	Required	C30	2.2 uF	2.2 uF		Internal LDO output stabilizing capacitor.	Placed close to the IC REGN pin. X7R capacitor is recommended.
VDDA	7	Required	C29	1 uF			Noise decoupling capacitor.	Placed close to the IC VDDA pin. X7R capacitor is recommended.
		Recommended	R18	10 Ω			Current limiting resistor.	
HDRV1	31	Required	Q1				Converter (Forward Buck Mode) High-Side N-Channel MOSFET gate driver. Recommended MOSFET is the CSD175R03A. This is also the reverse boost mode synchronous High-Side MOSFET. Refer to section 20.2.2.5 Power MOSFETs Selection in the BQ2571X datasheet for more details on the Power Stage MOSFET selection criterion.	
		Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Q1 High-Side MOSFET gate drive strength limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q1 turn-on and turn-off.	
LDRV1	29	Required	Q2				Converter (Forward Buck Mode) Low-Side N-Channel MOSFET. Recommended MOSFET is the CSD175R03A. This is also the reverse boost mode active Low-Side MOSFET. Refer to section 20.2.2.5 Power MOSFETs Selection in the BQ2571X datasheet for more details on the Power Stage MOSFET selection criterion.	
		Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Q2 Low-Side MOSFET gate drive strength limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q2 turn-on and turn-off. Sized to increase the effective E <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q2. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q2 are similar in magnitude.	
SW1-SW2, BTST1, BTST2	32-23, 30-15	Required	L1	1 uH	2.2 uH	3.3 uH	Converter inductor.	SW1 and SW2 should be connected to minimize the inductive path from the IC pin to the inductor, L1. Refer to section 20.2.2.2 Inductor Selection in the BQ2571X datasheet for more details on the inductor selection criterion.
		Required	C15	47 nF			Converter bootstrap capacitor for Q1 High-Side N-Channel MOSFET gate driver.	
		Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Bootstrap capacitor discharge current limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q1 turn-on.	
		Required	C16	47 nF			Converter bootstrap capacitor for Q4 High-Side N-Channel MOSFET gate driver.	
	Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Bootstrap capacitor discharge current limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q4 turn-on.		
HDRV2	34	Required	Q4				Converter (Forward Boost Mode) High-Side N-Channel MOSFET gate driver. Recommended MOSFET is the CSD175R03A. This is also the reverse boost mode active MOSFET. Refer to section 20.2.2.5 Power MOSFETs Selection in the BQ2571X datasheet for more details on the Power Stage MOSFET selection criterion.	
		Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Q4 High-Side MOSFET gate drive strength limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q4 turn-on and turn-off.	
LDRV2	26	Required	Q3				Converter (Forward Boost Mode) Low-Side N-Channel MOSFET gate driver. Recommended MOSFET is the CSD175R03A. This is also the reverse boost mode synchronous MOSFET. Refer to section 20.2.2.5 Power MOSFETs Selection in the BQ2571X datasheet for more details on the Power Stage MOSFET selection criterion.	
		Recommended	R <sub>th(sj-amb)</sub>	0 Ω			Q3 Low-Side MOSFET gate drive strength limiting resistor. For non-ideal layouts with EMI constraints, add an experimentally derived resistance to slow down the Q3 turn-on and turn-off. Sized to increase the effective E <sub>gs</sub> in comparison to the C <sub>gd</sub> of Q3. This helps prevent the Miller capacitance from driving the MOSFET gate during a high dV/dt event. This is more important when Q <sub>gs</sub> and Q <sub>gd</sub> of Q3 are similar in magnitude.	



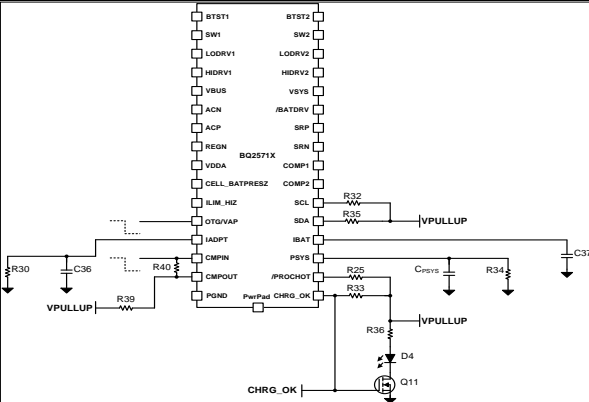
OUTPUT POWER - DESIGN CHECKLIST						
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION
<b>System output either from converter regulation of input source or battery</b>						
SYSTEM+ / SYSTEM-	Required	C5-C6/C7-C8/C9/C10/C21 (C5/C6/C7/C8/C9/C10/C21)	60 uF	80 uF		Forward Mode: Converter ceramic output filtering capacitors; Reverse Mode: Ceramic high frequency filtering input capacitors. For > 45 W to 65 W SYS load, use at least (8x) 10 uF capacitors with an extra (2x) 10 uF DNP. K7R capacitors are recommended.
	Required	C41-C49 (C41-C49)	33 uF	66 uF		Forward Mode: Converter tantalum polymer output filtering capacitors; Reverse Mode: Tantalum polymer high frequency filtering input capacitor. For > 65W SYS loads, with a 4S battery configuration, use at least (2x) 33 uF tantalum polymer capacitor. For > 90W SYS loads, with a 4S battery configuration, use at least (2x) 33 uF tantalum polymer capacitors.
<b>System output regulation sensing point</b>						
VSYS	Required	-	-	-	-	VSYS must be Kelvin connected to the output filter stage connected to SYSTEM+. The connection should be tied as close the output resonant filter portion of the system rail (C26/C27) as possible. Take precaution to not Kelvin connect this pin significantly far away from the output filter and/or IC VSYS pin, such that a large IR loss from the system load is sensed by VSYS.
	Recommended DNP	C41	10 uF			Noise decoupling capacitor. Placed close to the IC VSYS pin.
<b>Battery or battery pack connection to the charger</b>						
BATTERY+ / BATTERY-	Required	C26	10 uF	10 uF		Connected to the SRN pin, this capacitor is critical for accurate battery voltage sensing. From the SRN pin, the Constant Voltage (CV) phase of charging will regulate the voltage to the MaxChargeVoltage[Charge] Register setting. When charging is disabled and the SRN voltage is above the MinV[Charge] Register setting, the sensed voltage on the SRN pin is also used as a reference to regulate the SYS pin voltage such that: $V_{SYS} = V_{MAX} + 160\text{ mV}$ . K7R capacitor is recommended.
<b>Differential charge current sensing</b>						
SRP-SRN	Required	R8 (R <sub>ch</sub> )	10 mΩ	20 mΩ		For higher accuracy at light loads, increase to 20 mΩ. This will impact the BAT and P35 pins measurements. In Charge Current regulation for the Constant Current (CC) phase of charging, the CHG current is regulated as a differential voltage across R <sub>ch</sub> , such that $V_{CHG} = R_{ch} \times \text{ChargeCurrent}$ Register setting. If the charger is either in INDPM, WINDPM, Supplement Mode, or Thermal Foldback, the regulated charge current will be lower than the programmed value.
	Required	C28	1 uF	1 uF		Noise filter capacitor.
	Recommended	C27	0.1 uF			Differential mode noise filter.
	Recommended	R15, R16	10 Ω	10 Ω		Sized with a low power rating such that in the event of a reverse polarity event with the battery pack, the resulting unintended current flow will damage R15 or R16 first rather than the charger or the system. This acts as a crude form of reverse polarity protection.
<b>External battery MOSFET driver</b>						
/BATDRV	Required	Q7	-	-	-	External battery to system power path P-Channel MOSFET (BATFET).
	Recommended	R <sub>DS(on)</sub>	0 Ω			DS(on) value above threshold limiting resistor. Recommended MOSFET is the CSD2540Q23A.
<b>Converter external compensation networks</b>						
COMP1, COMP2	Required	C33	1800 pF			Average current control outer loop compensation network. Place close to the IC COMP1 pin.
	Required	R22	45.2 kΩ			Average current control outer loop high frequency filtering capacitor. Ideally connect the ground return of these components to a signal ground, rather than a power ground. If not possible, connect the ground return as close to the IC PGND pin as possible.
	Required	C31	33 pF			Average current control inner loop compensation network. Place close to the IC COMP2 pin.
	Required	R23	10 kΩ			Average current control inner loop high frequency filtering capacitor. Ideally connect the ground return of these components to a signal ground, rather than a power ground. If not possible, connect the ground return as close to the IC PGND pin as possible. When not using I <sub>1</sub> = 2.2 uA, scale R23 using $R23 = 10k\Omega \times I_{new} / 2.2\mu A$ .
	Required	C34	15 pF			Average current control inner loop high frequency filtering capacitor.

BQ2571X - Hardware Programmed Input Design



PIN						REQUIREMENT						COMPONENT						MIN						TYP						MAX						DESCRIPTION						COMMENTS AND RELEVANT EQUATIONS											
<p><b>Default charging and system parameter setting</b></p> <p>The CELL_BATPRESZ cell count settings is determined once VDDA is powered, typically after a valid input source is applied.</p> <p>If CELL_BATPRESZ is pulled LOW externally, this indicates to the charger that the battery has been removed. This will reset the ChargeCurrent() Register setting to 0mA.</p> <p>If enabled in the ProchotOption() Register setting, this will also trigger the ProchotStatus() register flag.</p>																																																					
CELL_BATPRESZ	18	Required	R24	*kΩ	Resistor divider network referenced to the VDDA rail to set the default charging voltage, default minimum system voltage, and maximum system voltage. Also input to signal charger of a battery absence.																		<table border="1"> <thead> <tr> <th>CELL COUNT</th> <th>PIN VOLTAGE w.r.t. VDDA</th> <th>BATTERY VOLTAGE MaxCharge(Voltage) Register</th> <th>MINIMUM SYSTEM VOLTAGE MinSystemVoltage() Register</th> <th>SYSOVP</th> </tr> </thead> <tbody> <tr> <td>45</td> <td>75%</td> <td>16.800 V</td> <td>12.288 V</td> <td>19.5 V</td> </tr> <tr> <td>35</td> <td>55%</td> <td>12.592 V</td> <td>9.216 V</td> <td>19.5 V</td> </tr> <tr> <td>25</td> <td>40%</td> <td>8.400 V</td> <td>6.144 V</td> <td>12 V</td> </tr> <tr> <td>15</td> <td>25%</td> <td>4.192 V</td> <td>3.584 V</td> <td>5 V</td> </tr> </tbody> </table>						CELL COUNT	PIN VOLTAGE w.r.t. VDDA	BATTERY VOLTAGE MaxCharge(Voltage) Register	MINIMUM SYSTEM VOLTAGE MinSystemVoltage() Register	SYSOVP	45	75%	16.800 V	12.288 V	19.5 V	35	55%	12.592 V	9.216 V	19.5 V	25	40%	8.400 V	6.144 V	12 V	15	25%	4.192 V	3.584 V	5 V
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ILIM_HIZ	6	Required	R19	*kΩ	Resistor divider network to set an external input current limit.																		<p><b>External input current limit setting and converter high impedance control</b></p> <p>The voltage set at this pin through the resistor divider network determines the externally set input current limit setting.</p> $V_{ILIM\_HIZ} = 1V + 40 \times IINDPM_{setting} \times R_{AC}, \text{ where } 1.2V < V_{ILIM\_HIZ} < 4.0V$																														
			R27	*kΩ																																																	
		Recommended CAP	C35	*nF	Noise decoupling capacitor																		Place close to the IC ILM_HIZ pin.																														
IADPT	8	Required	R30	3%	*Ω	+3%	Resistor used to indicate inductor selection and output an analog input current measurement																		<p><b>Inductor selection setting and input current measurement output</b></p> <table border="1"> <thead> <tr> <th>INDUCTOR IN USE</th> <th>RESISTOR ON IADPT PIN</th> </tr> </thead> <tbody> <tr> <td>1 μH</td> <td>93 kΩ</td> </tr> <tr> <td>2.2 μH</td> <td>137 kΩ</td> </tr> <tr> <td>3.3 μH</td> <td>169 kΩ</td> </tr> </tbody> </table>						INDUCTOR IN USE	RESISTOR ON IADPT PIN	1 μH	93 kΩ	2.2 μH	137 kΩ	3.3 μH	169 kΩ															
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		Recommended CAP	C36	100 pF	Noise decoupling capacitor																		Place close to the IC IADPT pin.																														

**BQ2571X - Communication and Miscellaneous Input/Output Signal Design**



COMMUNICATION AND MISC INPUT/OUTPUT SIGNAL - DESIGN CHECKLIST						COMMENTS AND RELEVANT EQUATIONS	
PIN NAME	REQUIREMENT	COMPONENT	MIN	TYP	MAX	DESCRIPTION	COMMENTS AND RELEVANT EQUATIONS
<b>Reverse mode On-The-GO (OTG) or Vmin Active Protection (VAP) mode enable</b>							
OTG/VAP	5	Optional	-	-	-	OTG or VAP mode	Full HIGH to enable OTG or VAP mode, based on the ChargeOption(3), OTG(Voltage), and OTG(Current) registers. Pull LOW to disable OTG or VAP mode.
<b>Inductor selection setting and analog calculated input current measurement output</b>							
IADPT	8	Required	R30	3%	*Q	+3%	Resistor used to indicate inductor selection and output an analog input current measurement
		Recommended	C36	100	pF		Noise decoupling capacitor
<b>Independent comparator input and output</b>							
CMPIN, CMPOUT	14, 15	Optional	R39, R40	10 kΩ, 1 MΩ			Pullup resistor for CMPOUT open-drain output Resistor for when independent comparator is not used
<b>I2C or SMBus Open-drain communication input and output</b>							
SCL, SDA	13, 12	Required	R32, R35	10	kΩ		Pullup resistors for the open-drain I2C or SMBus clock and data communication bus
<b>Analog battery current measurement output</b>							
IBAT	9	Optional	C37	100	pF		Analog voltage output representing the battery charge or discharge current measurement
<b>Analog system power measurement output</b>							
PSYS	10	Optional	R34, C38	30.1 kΩ, 100 pF			The PSYS_RATIO setting is programmable in the ChargeOption(1) Register. Proper PSYS functionality is limited to use with either a 10 mΩ or 20 mΩ for either R46 and R49. Select the appropriate R46/R49 resistance value in the ChargeOption(1) Register. In reverse OTG mode, PSYS either measure the total battery output power or the system power, which can be set in the ChargeOption(3) register. The PSYS calculation assumes 100% efficiency.
/PROCHOT	11	Optional	R25	10	kΩ		Pullup resistor for/PROCHOT open-drain output
<b>Active LOW open-drain output signal for Processor Hot flags</b>							
CHRG_OK	4	Optional	R33, R36, D4, Q11				Pullup resistor for CHRG_OK open-drain output CHRG_OK LED indication control
<b>IC Thermal dissipation pad</b>							
PwrPad	-	Required	-	-	-	-	Main point of heat dissipation for the IC

$$V_{IADPT} = IADPT\_GAIN \times V_{ACP-ACN}, \text{ when in forward mode}$$

$$V_{IADPT} = IADPT\_GAIN \times V_{ACN-ACP}, \text{ when in reverse OTG mode}$$

$$V_{IBAT} = IBAT\_GAIN \times V_{SRP-SRN}, \text{ when battery is charging}$$

$$V_{IBAT} = IBAT\_GAIN \times V_{SRN-SRP}, \text{ when battery is discharging}$$

$$V_{PSYS} = R34 \times PSYS\_RATIO \times (V_{ACP-IN} + V_{SRN-BAT})$$